

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

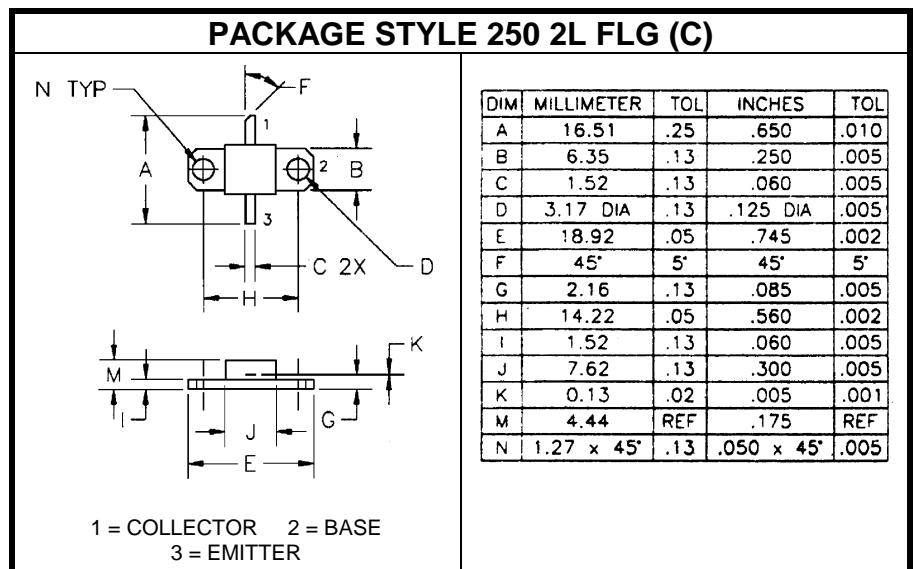
The **ASI MRA1417-2** is a Common Base Device Designed for Class C Power Amplifier Applications up to 1.7 GHz.

FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	0.5 A
V_{CB0}	50 V
P_{DISS}	12 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	15 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 20\text{ mA}$	50			V
BV_{EBO}	$I_E = 0.25\text{ mA}$	3.5			V
I_{CBO}	$V_{CB} = 28\text{ V}$			0.5	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$ $I_C = 100\text{ mA}$	10		100	---
C_{ob}	$V_{CB} = 28\text{ V}$ $f = 1.0\text{ MHz}$			4.5	pF
P_G	$V_{CE} = 28\text{ V}$ $P_{OUT} = 2.0\text{ W}$ $f = 1700\text{ MHz}$	8.0			dB
η_c		45			%